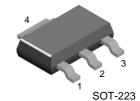


# BCP51

# **PNP General Purpose Amplifier**

- This device is designed for general purpose medium power amplifiers and switches requiring collecor currents to 1.0A.
- Sourced from process 77.



1. Base 2. Collector 3. Emitter

# **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	✓ Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>CBO</sub>	Collector-Base Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V
I <sub>C</sub>	Collector Current - Continuous	-1.5	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above whitch the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
  These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units		
Off Characte	Off Characteristics						
V <sub>(BR)CEO</sub>	Collector-Emitter Sustaining Voltage	$I_C = -10 \text{mA}, I_B = 0$	-45		V		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	-45		V		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5.0		V		
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$ $V_{CB} = -30V, I_{E} = 0, T_{a} = 125^{\circ}C$		-100 -10	nA μA		
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5.0V, I_{C} = 0$		-10	μΑ		
On Characte	eristics						
h <sub>FE</sub>	DC Current Gain	$I_C = -5.0$ mA, $V_{CE} = -2.0$ V $I_C = -150$ mA, $V_{CE} = -2.0$ $I_C = -50$ 0mA, $V_{CE} = -2.0$ V	25 40 25	250			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA		-0.5	V		
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = -500mA, V <sub>CE</sub> = -2.0V		-1.0	V		

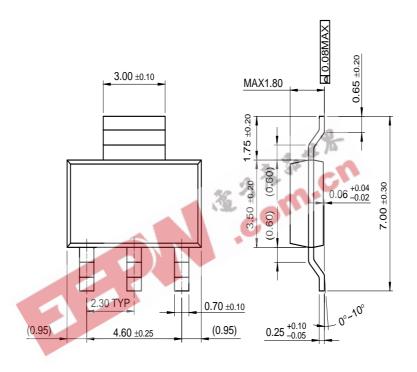
# Thermal Characteristics T<sub>a</sub>=25°C unless otherwise noted

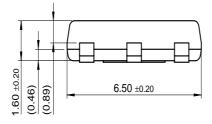
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

<sup>\*</sup> Device mounted on FR-4PCB 36mm x 18mm x 1.5mm; mounting pad for the collector lead min. 6cm<sup>2</sup>.

# **Package Dimensions**

# **SOT-223**





Dimensions in Millimeters

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### PRODUCT STATUS DEFINITIONS

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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